



FIG. 6(A)

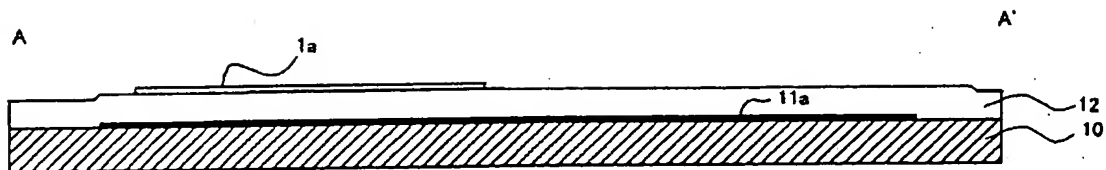


FIG. 6(B)

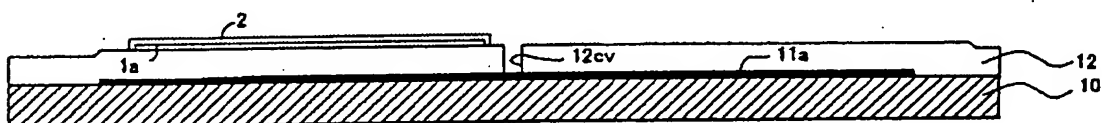


FIG. 6(C)

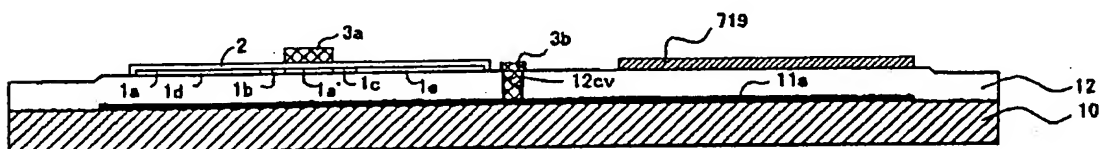


FIG. 6(D)

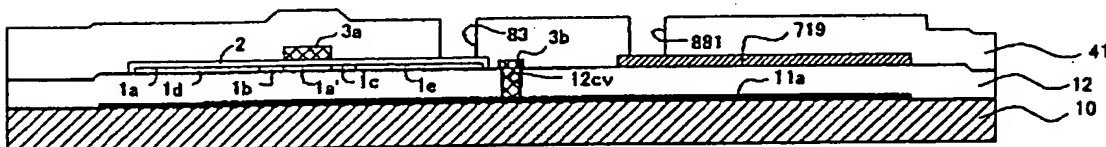
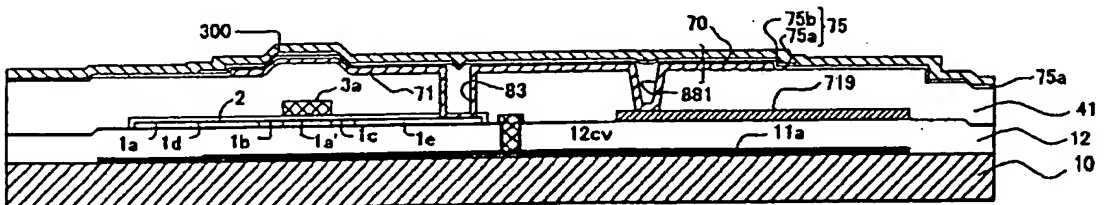


FIG. 6(E)



[illegible]

This cross-sectional diagram illustrates a complex semiconductor device structure. The base consists of a substrate (10) with a layer (12) and a patterned layer (11a). Above this is a series of layers including 12cv, 1e, 1c, 1b, 1d, and 1a. A central component (801) is surrounded by various structures: 70, 71, 719, 75b, 75a, 882, 804, 6a1, 6a2, 803, 89, 402, 44, 43, 42, 41, 400, 41TN, 300, 81, 2, 3a, 71, 83, 3b, 12cv, 11a, 1e, 1c, 1b, 1d, 1a, 75a, 6a, 9a, 50, 22, 21, and 20. The entire assembly is covered by a top layer (20).